



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23-3L Plastic-Encapsulate Transistors

2SA1464 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.2 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.5 A

Collector-base voltage

$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-23-3L



1. BASE
2. EMITTER
3. COLLECTOR

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-2V, I_C=-150mA$	75	140	300	
DC current gain	$h_{FE(2)}$	$V_{CE}=-2V, I_C=-500mA$	20	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$		-0.45	-0.75	V
Base-emitter voltage	$V_{BE(on)}$	$I_C=-500mA, V_{CE}=-50V$		-1.0	-1.3	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-20mA$	150	400		MHz
Output Capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		5.0	8.0	pF
Turn-on Time	t_{on}	$V_{CC}=-30V$ $I_C=-150mA$ $I_{B1}=-I_{B2}=-15mA$			35	ns
Storage Time	t_{stg}				225	ns
Turn-on Time	T_{off}				255	ns

CLASSIFICATION OF $h_{FE(1)}$

Marking	Y12	Y13	Y14
Range	75-150	100-200	150-300